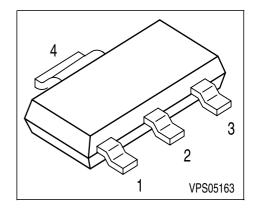


PNP Silicon High Voltage Transistor

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: PZTA42 (NPN)



Туре	Marking	Pin Configuration				Package
PZTA92	PZTA 92	1=B	2=C	3=E	4=C	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit V	
Collector-emitter voltage	V _{CEO}	300		
Collector-base voltage	V_{CBO}	300		
Emitter-base voltage	V _{EBO}	5		
DC collector current	I _C	500	mA	
Base current	l _B	100		
Total power dissipation, T_S = 124 °C	P _{tot}	1.5	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-65 150		

Thermal Resistance

Junction - soldering point 1)	R _{th,IS}	≤17	K/W

1

 $^{^{1}\}mbox{For calculation of}\,\mbox{\it R}_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

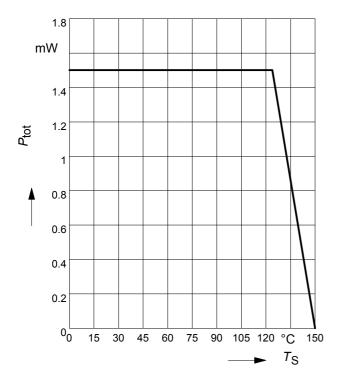
Parameter	Symbol	Values			Unit
			typ.	max.	†
DC Characteristics				•	•
Collector-emitter breakdown voltage	V _{(BR)CEO}	300	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	$V_{(BR)CBO}$	300	-	-	
$I_{\rm C}$ = 100 μ A, $I_{\rm E}$ = 0					
Emitter-base breakdown voltage	V _{(BR)EBO}	5	-	-	
$I_{\rm E}$ = 10 μ A, $I_{\rm C}$ = 0					
Collector cutoff current	I _{CBO}	-	-	250	nA
$V_{\rm CB}$ = 200 V, $I_{\rm E}$ = 0					
Collector cutoff current	I _{CBO}	-	-	20	μΑ
V_{CB} = 200 V, I_{E} = 0 , T_{A} = 150 °C					
Emitter cutoff current	I _{EBO}	-	-	100	nA
$V_{\text{EB}} = 3 \text{ V}, I_{\text{C}} = 0$					
DC current gain 1)	h _{FE}				-
$I_{\rm C}$ = 1 mA, $V_{\rm CE}$ = 10 V		25	-	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 10 V		40	-	-	
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 10 V		25	-	-	
Collector-emitter saturation voltage1)	V _{CEsat}	-	-	0.5	V
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
Base-emitter saturation voltage 1)	V _{BEsat}	-	-	0.9	
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
AC Characteristics	,				
Transition frequency	f _T	-	100	-	MHz
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 10 V, f = 100 MHz					
Collector-base capacitance	C _{cb}	-	-	6	pF
V_{CB} = 20 V, f = 1 MHz					

2

¹⁾ Pulse test: $t < 300 \mu s$; D < 2%

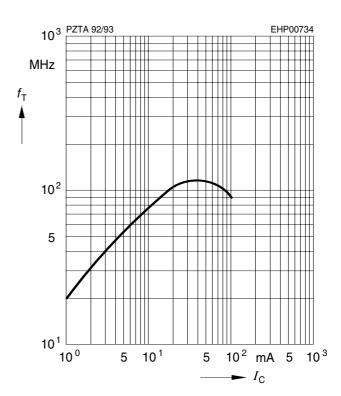


Total power dissipation $P_{tot} = f(T_S)$



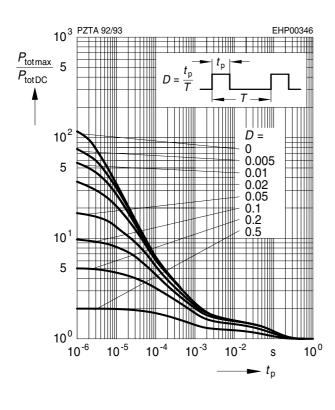
Transition frequency $f_T = f(I_C)$

$$V_{CE} = 10V, f = 100MHz$$



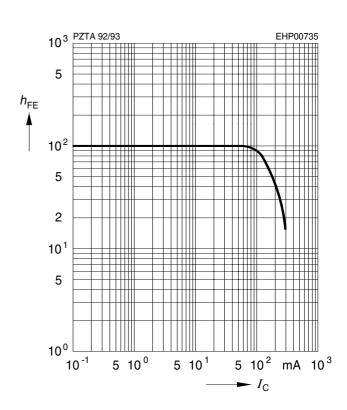
Permissible pulse load

$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$$



DC current gain $h_{FE} = f(I_C)$

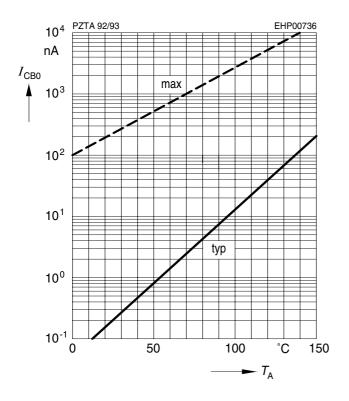
$$V_{CE} = 10V$$





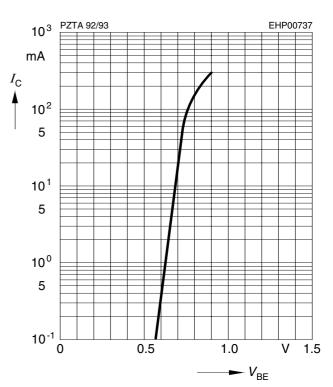
Collector cutoff current $I_{CBO} = f(T_A)$

$$V_{CB} = 200V$$



Collector current $I_{C} = f(V_{BE})$

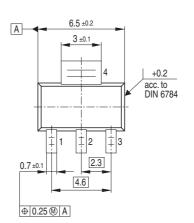
$$V_{CE}$$
 = 10V

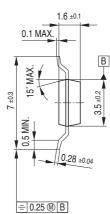




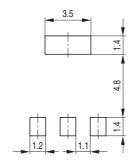
Package Outline



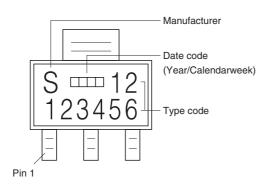


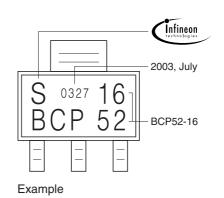


Foot Print



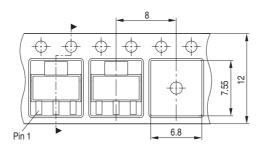
Marking Layout





Packing

Code E6327: Reel ø180 mm = 1.000 Pieces/Reel Code E6433: Reel ø330 mm = 4.000 Pieces/Reel







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